

Thyristor Module

$$V_{RRM} = 1200\text{ V}$$

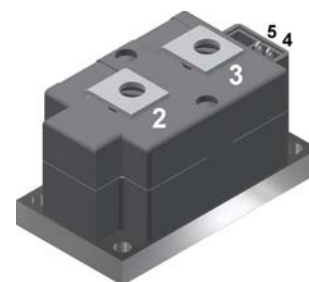
$$I_{TAV} = 560\text{ A}$$

$$V_T = 1,01\text{ V}$$

Single Thyristor

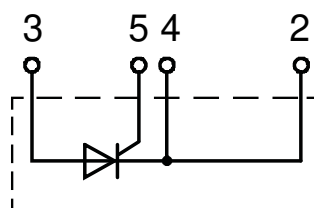
Part number

MCO500-12io1



Backside: isolated

 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al₂O₃-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: Y1

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

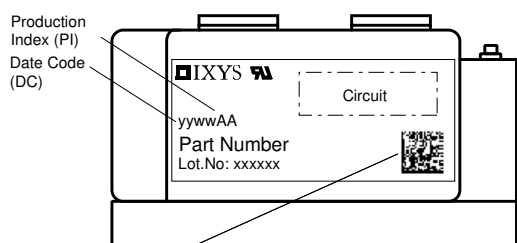
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Thyristor				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			2	mA
		$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$			40	mA
V_T	forward voltage drop	$I_T = 500\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1,08	V
		$I_T = 1000\text{ A}$				1,27	V
		$I_T = 500\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1,01	V
		$I_T = 1000\text{ A}$				1,24	V
I_{TAV}	average forward current	$T_C = 85^{\circ}\text{C}$	$T_{VJ} = 140^{\circ}\text{C}$			560	A
$I_{T(RMS)}$	RMS forward current	180° sine				880	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 140^{\circ}\text{C}$			0,80	V
r_T	slope resistance					0,38	mΩ
R_{thJC}	thermal resistance junction to case					0,072	K/W
R_{thCH}	thermal resistance case to heatsink				0,024		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			1600	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			17,0	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			18,4	kA
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$			14,5	kA
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			15,6	kA
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			1,45	MA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1,40	MA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^{\circ}\text{C}$			1,04	MA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1,01	MA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		876		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 140^{\circ}\text{C}$			120	W
		$t_p = 300\text{ }\mu\text{s}$				60	W
P_{GAV}	average gate power dissipation					20	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 1500\text{ A}$				100	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 1\text{ A}/\mu\text{s};$ $I_G = 1\text{ A}; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 500\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$			1000	V/ μs
		$R_{GK} = \infty$; method 1 (linear voltage rise)					
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			2	V
			$T_{VJ} = -40^{\circ}\text{C}$			3	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			300	mA
			$T_{VJ} = -40^{\circ}\text{C}$			400	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}\text{C}$			0,25	V
I_{GD}	gate non-trigger current					10	mA
I_L	latching current	$t_p = 30\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			400	mA
		$I_G = 1\text{ A}; di_G/dt = 1\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			300	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 1\text{ A}; di_G/dt = 1\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 500\text{ A}; V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^{\circ}\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}; dv/dt = 50\text{ V}/\mu\text{s}; t_p = 200\text{ }\mu\text{s}$			350		μs

Package Y1			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			600	A
T_{VJ}	virtual junction temperature		-40		140	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				650		g
M_D	mounting torque		4,5		7	Nm
M_T	terminal torque		11		13	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	16,0			mm
$d_{Spb/Apb}$		terminal to backside	25,0			mm
V_{ISOL}	isolation voltage	t = 1 second	4800			V
		t = 1 minute	4000			V



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCO500-12io1	MCO500-12io1	Box	2	463728

Similar Part	Package	Voltage class
MCO500-14io1	Y1-2-CU	1400
MCO500-16io1	Y1-2-CU	1600
MCO500-18io1	Y1-2-CU	1800
MCO600-20io1	Y1-2-CU	2000

MCO600-22io1	Y1-2-CU	2200
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Equivalent Circuits for Simulation		* on die level	$T_{VJ} = 140^{\circ}\text{C}$
		Thyristor	
$V_{0\max}$	threshold voltage	0,8	V
$R_{0\max}$	slope resistance *	0,22	mΩ

Thyristor

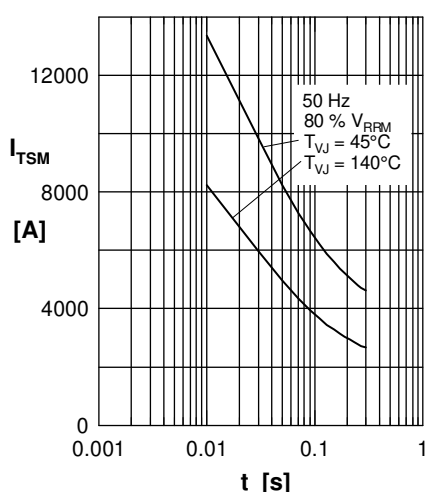


Fig. 1 Surge overload current
 I_{TSM} : Crest value, t : duration

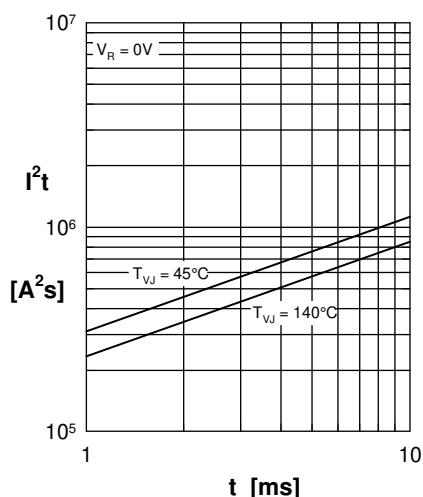


Fig. 2 I^2t versus time (1-10 ms)

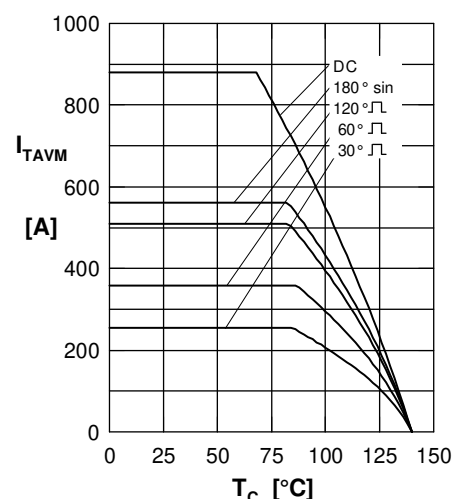


Fig. 3 Maximum forward current at case temperature

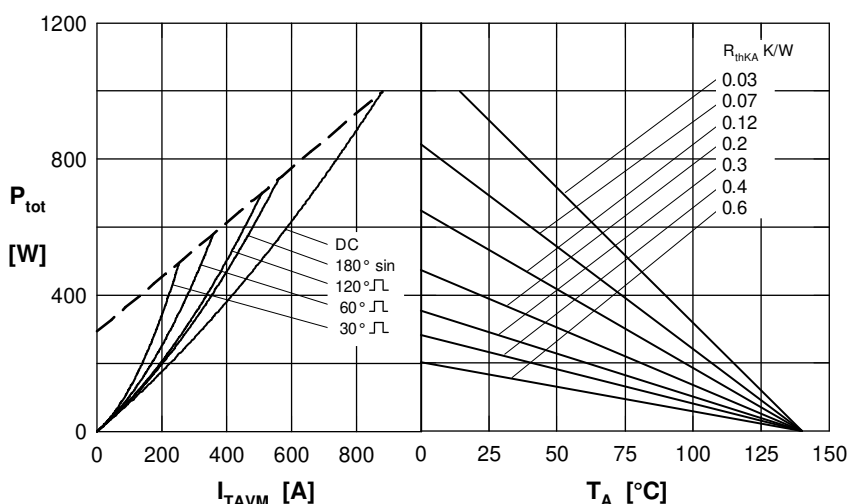


Fig. 4 Power dissipation versus on-state current & ambient temperature

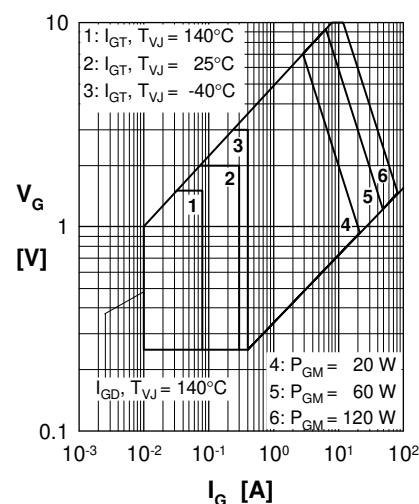


Fig. 5 Gate trigger characteristics

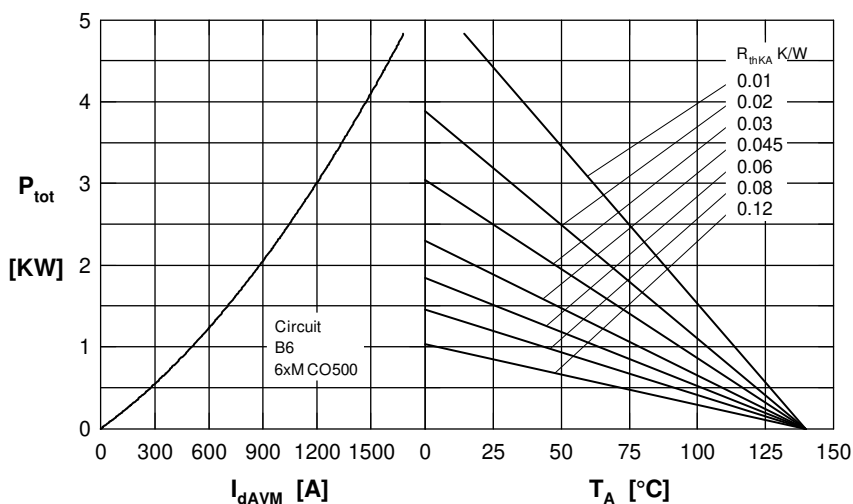


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

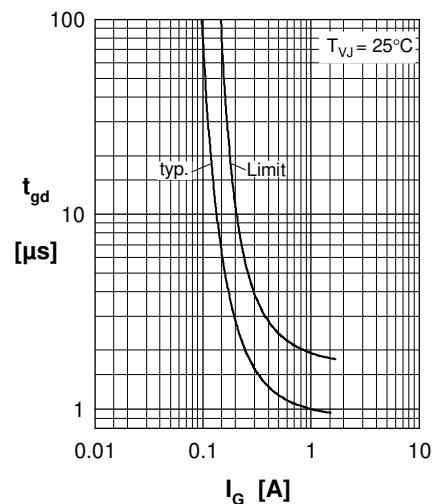


Fig. 7 Gate trigger delay time

Thyristor

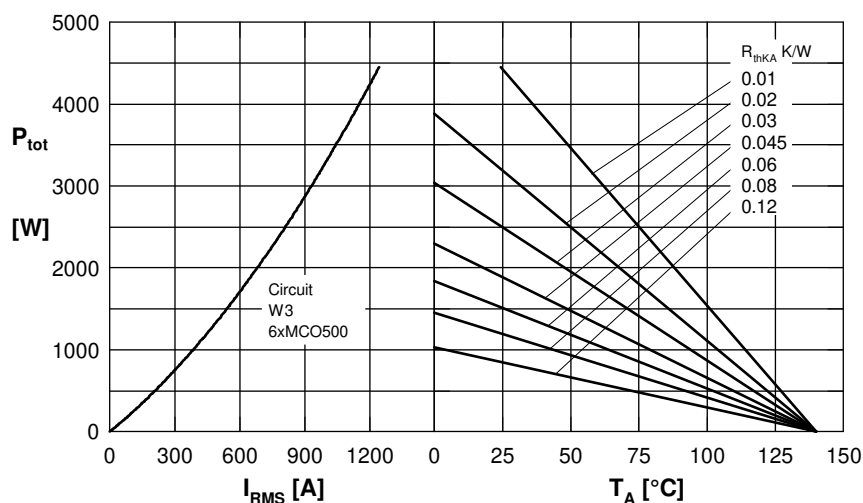


Fig. 8 Three phase AC-controller: Power dissipation versus RMS output current and ambient temperature

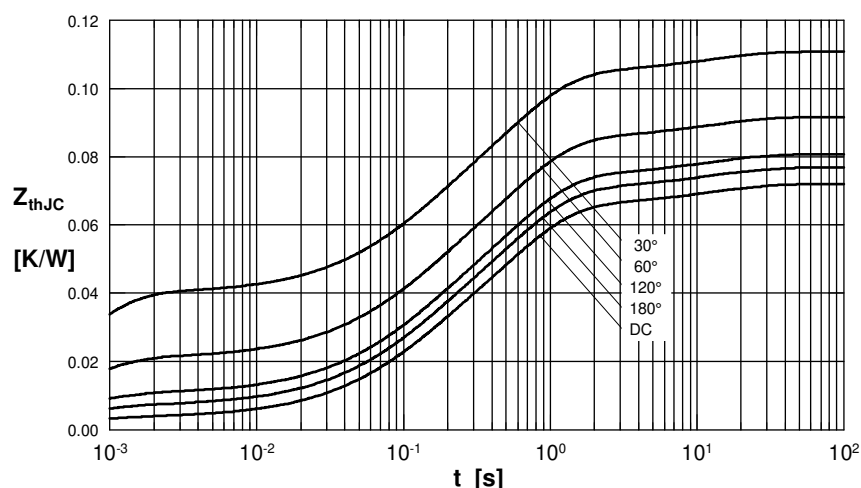


Fig. 9 Transient thermal impedance junction to case

R_{thJC} for various conduction angles d:

d	R_{thJC} (K/W)
DC	0.072
180°	0.0768
120°	0.081
60°	0.092
30°	0.111

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0035	0.0054
2	0.0186	0.098
3	0.0432	0.54
4	0.0067	12

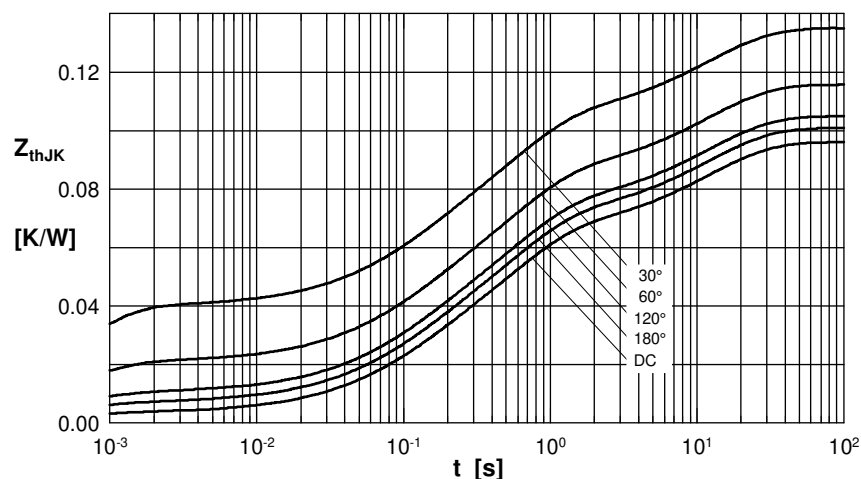


Fig.10 Transient thermal impedance junction to heatsink

R_{thJK} for various conduction angles d:

d	R_{thJK} (K/W)
DC	0.096
180°	0.1
120°	0.105
60°	0.116
30°	0.135

Constants for Z_{thJK} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.0035	0.0054
2	0.0186	0.098
3	0.0432	0.54
4	0.0067	12
5	0.024	12